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Please Amend the second paragraph on page 2 beginning on line 13 as follows:

As for the single crystal thin films, it is common that they are epitaxially grown using a single crystal substrate. For example, there have been reported that GaN-based single crystal thin films are formed on a single crystal sapphire substrate by an MOCVD (Metal Organic Chemical Vapor Deposition) method or by a gas source MBE method (Molecular Beam Epitaxial Method), or on a SiC substrate by a low pressure metal organic vapor phase epitaxy (see, Kiyoteru Yoshida "Electronic devices using GaN" OYOBUTURI Vol.68, No.7, pp.790 and 798 pp. 787-792 and Kuramata et al., "Continuous-Wave Operation InGaN Laser Diodes On SiC Substrates," pp. 797-800, OYOBUTURI, Vol. 68, No. 7, published by The Japan Society of Applied Physics, July 10, 1999). As for the oxide-based single crystal thin films, their epitaxial thin films are formed on a substrate composed of single crystal strontium titanate (SrTiO_3 : STO), single crystal lanthanum aluminate (LaAlO_3 :LAO) or single crystal sapphire substrate by a sputtering or PLD method (Pulsed Laser Deposition).

Please Amend the second paragraph on page 15 beginning on line 10 as follows:

Figs. 6A and 6B show patterns when an electron beam is launched into the Si[01 $\bar{1}$] and Si[010] directions. Fig. 6A illustrates RHEED observation results of the MnS/Si (100) thin films. They exhibit a streak pattern, and it is seen from the spacing between the acceleration voltage (25 kV) of the incident electron beam and the streak that the lattice constant of MnS is about 5.2 Å, which nearly equal to the value 5.209 Å given by the foregoing relevant document (Kiyoteru Yoshida "Electronic devices using GaN", OYOBU TURI Vol.68, No.7, pp.790 and 798, published by The Japan Society of Applied Physics, July 10, 1999) (JUZA et al., "Solid Solution in Systems ZnS/MnS, ZnSe/MnSe and ZnTe/MnTe," Journal of Inorganic and General Chemistry, Vol. 285, pp. 61-69, 1956). Fig. 6B illustrates the RHEED observation results of the AlN/MnS/Si (100) thin films in the [$\bar{1}$ 100] direction and [0001] direction of the AlN thin film, respectively.